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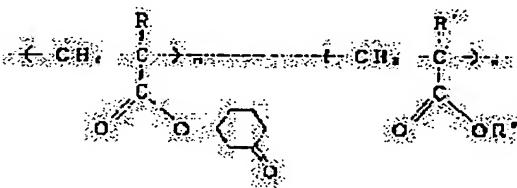
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## (54) RESIST COMPOSITION AND PATTERN FORMING METHOD USING IT

### (57)Abstract:

**PURPOSE:** To provide a radiation resist compsn. having high sensitivity and dry etching resistance by incorporating a copolymer containing 3-oxocyclohexyl acrylate or methacrylate monomers as the repeating unit.

**CONSTITUTION:** This radiation resist compsn. contains a copolymer expressed by formula having 3-oxocyclohexyl acrylate or methacrylate monomer unit, and preferably, other acrylate or methacrylate monomer unit as the repeating unit. In formula, R and R' are H or CH<sub>3</sub> and R'' is an org. acid. If this compsn. is prepared to obtain a resist material, R'' is preferably an alicyclic org. group, for example, adamantyl group, norbonyl group, or cyclohexyl group in order to obtain small absorption in a short wavelength region and high dry etching durability. The weight average mol.wt. of this copolymer is preferably 2000 to 3000000.



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